

isc Silicon PNP Power Transistor**2SA965****DESCRIPTION**

- Power amplifier applications
- Driver stage amplifier applications

APPLICATIONS

- Designed for Switching and amplification

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-120	V
V_{CEO}	Collector-Emitter Voltage	-120	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-0.8	A
P_C	Collector Power Dissipation @ $T_a < 50^{\circ}\text{C}$	-0.9	W
J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}\text{C}$

isc Silicon NPN Power Transistor

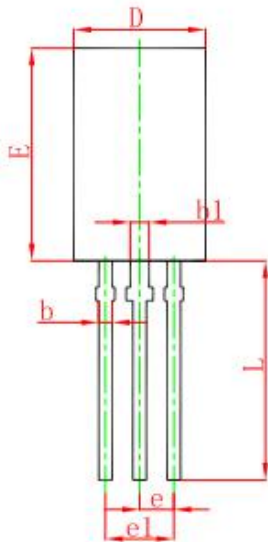
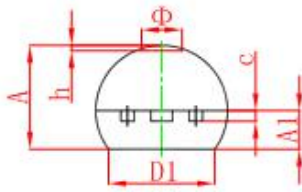
2SA965

ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO}	Collector-base breakdown Voltage	I _C = -10mA; I _E = 0	-120			V
V _{EBO}	Emitter-base breakdown Voltage	I _E = -1mA; I _C = 0	-5			v
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -500mA; I _B = -50mA			-1.0	V
V _{BE(on)}	Base-Emitter on Voltage	V _{CE} = -5V, I _C = -500mA			-1.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -120V; I _E = 0			-100	nA
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5V; I _C = 0			-100	nA
h _{FE}	DC Current Gain	I _C =-100mA; V _{CE} = -5V	-80		-240	

TO-92MOD Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.800	5.000	0.189	0.197
A1	1.730	2.030	0.068	0.080
b	0.440	0.600	0.017	0.024
b1	0.940	1.100	0.037	0.043
c	0.350	0.450	0.014	0.018
D	5.900	6.100	0.232	0.240
D1	4.000		0.157	
E	8.500	8.700	0.335	0.343
e	1.500 TYP.		0.059 TYP.	
e1	2.900	3.100	0.114	0.122
L	13.800	14.200	0.543	0.559
Φ		1.600		0.063
h	0.000	0.380	0.000	0.015

